

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-7. (Canceled)

8. (Currently Amended) A method of producing an SOI wafer having a buried oxide film with a thickness of less than 100 nm, comprising:

forming an oxide film having a thickness of 100 nm or more on a surface of at least one of a bond wafer and a base wafer, bonding the bond wafer to the base wafer through the formed oxide film, and making the bond wafer into a thin film, wherein after the oxide film is formed so that the total thickness of the oxide film formed on the surface of at least one of the bond wafer and the base wafer is thicker than a thickness of the buried oxide film that the SOI wafer to be produced has, the bond wafer is bonded to the base wafer through the formed oxide film, the bond wafer is made into a thin film to form an SOI layer, and thereafter, an obtained bonded wafer is subjected to heat treatment for 4 hours or more to reduce the thickness of the buried oxide film by 20 nm or more, and the thickness of the buried oxide film is reduced to less than 100 nm.

9. (Previously Presented) The method of producing an SOI wafer according to Claim 8, wherein a thickness of the SOI layer formed by making the bond wafer into a thin film is 500 nm or less.

10. (Previously Presented) The method of producing an SOI wafer according to Claim 8, wherein the heat treatment to reduce the thickness of the buried oxide film is performed in an atmosphere of a hydrogen gas, an argon gas, or a mixed gas of those at a temperature of 1000 °C or more.

11. (Previously Presented) The method of producing an SOI wafer according to Claim 9, wherein the heat treatment to reduce the thickness of the buried oxide film is

performed in an atmosphere of a hydrogen gas, an argon gas, or a mixed gas of those at a temperature of 1000 °C or more.

12–15. (Canceled)

16. (Previously Presented) The method of producing an SOI wafer according to Claim 8, wherein before the bond wafer is bonded to the base wafer, hydrogen ions or rare gas ions are implanted into a surface layer portion of the bond wafer to form an ion-implanted layer, and after the ion-implanted surface of the bond wafer is bonded to the base wafer, the bond wafer is delaminated at the formed ion-implanted layer to make the bond wafer into a thin film.

17. (Previously Presented) The method of producing an SOI wafer according to Claim 9, wherein before the bond wafer is bonded to the base wafer, hydrogen ions or rare gas ions are implanted into a surface layer portion of the bond wafer to form an ion-implanted layer, and after the ion-implanted surface of the bond wafer is bonded to the base wafer, the bond wafer is delaminated at the formed ion-implanted layer to make the bond wafer into a thin film.

18. (Previously Presented) The method of producing an SOI wafer according to Claim 10, wherein before the bond wafer is bonded to the base wafer, hydrogen ions or rare gas ions are implanted into a surface layer portion of the bond wafer to form an ion-implanted layer, and after the ion-implanted surface of the bond wafer is bonded to the base wafer, the bond wafer is delaminated at the formed ion-implanted layer to make the bond wafer into a thin film.

19. (Previously Presented) The method of producing an SOI wafer according to Claim 11, wherein before the bond wafer is bonded to the base wafer, hydrogen ions or rare gas ions are implanted into a surface layer portion of the bond wafer to form an ion-implanted layer, and after the ion-implanted surface of the bond wafer is bonded to the base wafer, the

bond wafer is delaminated at the formed ion-implanted layer to make the bond wafer into a thin film.

20–23. (Canceled)

24. (Previously Presented) The method of producing an SOI wafer according to Claim 8, wherein after the heat treatment to reduce the thickness of the buried oxide film is performed, sacrificial oxidation treatment is further performed.

25. (Previously Presented) The method of producing an SOI wafer according to Claim 9, wherein after the heat treatment to reduce the thickness of the buried oxide film is performed, sacrificial oxidation treatment is further performed.

26. (Previously Presented) The method of producing an SOI wafer according to Claim 10, wherein after the heat treatment to reduce the thickness of the buried oxide film is performed, sacrificial oxidation treatment is further performed.

27. (Previously Presented) The method of producing an SOI wafer according to Claim 11, wherein after the heat treatment to reduce the thickness of the buried oxide film is performed, sacrificial oxidation treatment is further performed.

28–31. (Canceled)

32. (Previously Presented) The method of producing an SOI wafer according to Claim 16, wherein after the heat treatment to reduce the thickness of the buried oxide film is performed, sacrificial oxidation treatment is further performed.

33. (Previously Presented) The method of producing an SOI wafer according to Claim 17, wherein after the heat treatment to reduce the thickness of the buried oxide film is performed, sacrificial oxidation treatment is further performed.

34. (Previously Presented) The method of producing an SOI wafer according to Claim 18, wherein after the heat treatment to reduce the thickness of the buried oxide film is performed, sacrificial oxidation treatment is further performed.

35. (Previously Presented) The method of producing an SOI wafer according Claim 19, wherein after the heat treatment to reduce the thickness of the buried oxide film is performed, sacrificial oxidation treatment is further performed.

36–39. (Canceled)

40. (Previously Presented) An SOI wafer produced by the method of producing an SOI wafer according to Claim 8.

41. (Canceled)